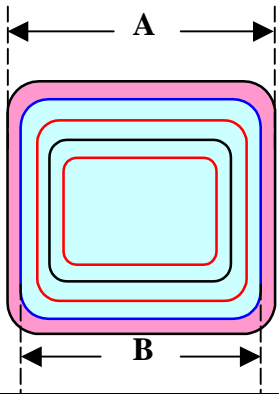


Features : <ul style="list-style-type: none"> * Extremely low forward volts * Guard ring protection * Low reverse leakage current 	Chip size(A):	0.814 * 0.814 mm ²		
	Bond Pad size(B) :	0.686 * 0.686 mm ²		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
Electrical Characteristics		Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C		VF max	0.68	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C		VR min.	63	Volt.
Minimum Non-repetitive Peak Surge current at 25°C		IFSM	25	Amp
Storage Temperature		TSTG	-65 to +125	°C

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